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Sheet 1 of 1

ATTORNEY DOCKET NO.	SERIAL NO.
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APPLICANT	
Valerie BOUSQUET, et al.	
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U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
		Japanese Office Action dated July 10, 2009.
		Selkoh Yoshida, "Photoluminescence measurement of InGaN and GaN grown by a gas-source molecular-beam epitaxy method", J. Appl. Phys., Vol. 81, No. 12, pp. 7966-7969 (1997).
		N. Grandjean, et al., "Real time control of In _x Ga _{1-x} N molecular beam epitaxy growth", Appl. Phys. Lett., Vol. 72, No. 9, pp. 1078-1080 (1998).

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